

HL1361CPxx

DFB Laser Diode Chip

Sample Categories and Disclaimer

Functional sample that has the suffix of "-F" or "-Fx" to the product number is a sample that is designed according to the customer's request. The purpose of this sample is to check and confirm the product feasibility. Thus the sample may be an R&D prototype or may be a modified current product. This sample may not be manufactured in qualified production lines nor using qualified parts. Basically Oclaro guarantees the requested performance of BOL (Beginning Of Life). Any qualification will not be applied.

Working sample that has the suffix of "-W" or "-Wx" to the product number is a sample to evaluate, confirm and finalize the product specifications. Basically Oclaro guarantees the performance of BOL (Beginning Of Life). Not all qualifications may be completed. This sample may not be manufactured in qualified production lines nor be using qualified components. Until Oclaro Inc. releases the products for general sales, Oclaro Inc. reserves the right to change prices, features, functions, specifications, capabilities and release schedule.

DESCRIPTION

General

The HL1361CPxxis a Distributed Feed-Back (DFB) laser diode chip. Individual chip is designed for 10Gbit/s operation and for use in the dry N2 hermetic sealed package.

PN information

PN*	Wavelength** (nm)		
HL1361CPxx	1310		

^{*&}quot;xx" will be assigned separately: for example "20" or "30"

Pin Configurations



Fig 1. Block Diagram (one LD chip)

Table 1. Pin Configurations

Pin#	Description	Remarks
1	Laser anode (P electrode)	
2	Laser cathode (N electrode)	

^{*} Actual wavelength range is specified separately.



MECHANICAL DIMENSIONS

Individual chip size is 250 μ m x 200 μ m x 92 μ m. Fig. 4 shows a chip outline and metallization pattern. The Anode has typ. 0.55 μ m Au film and Cathode has typ. 0.57 μ m Au film respectively.

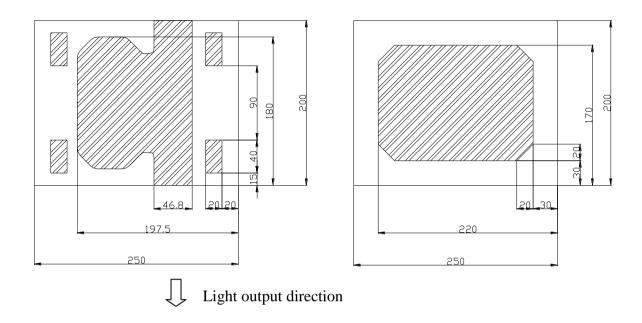
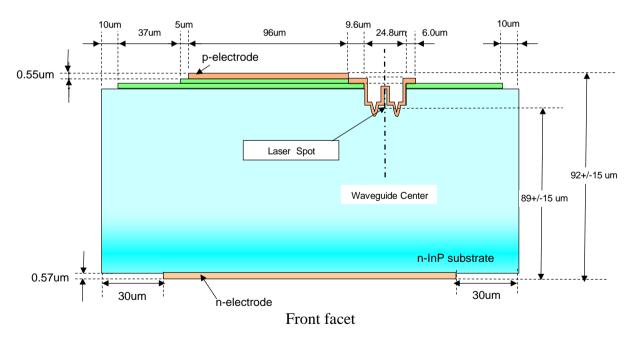


Fig.2 Top view (Anode)

Fig.3 Bottom view (Cathode)



(Outline: +/-20um)

Fig 4 Chip Outline and Dimensions



PERFORMANCE SPECIFICATIONS

Absolute Maximum Ratings

Since the HL1361CPxx is a chip form, the performance will depend on not only chip performance but also its assembling process. If the chip is assembled in a proper way, the performance described in Table 2 can be expected but these are not guaranteed values. Oclaro assumes no responsibility for those reliability when they are assembled and/or tested in customer Tc means submount temperature when the chip mounted on Oclaro standard sub-mount soldered on heat sink.

Table 2. Absolute Maximum Ratings (Tc=25°C, unless otherwise specified)

	Absolute Maximum Rating		Max	Unit	
1	1 Storage temperature		85	C	
2	2 Operating temperature		95	C	
3	3 Laser forward bias current		150	mA	
4	4 Laser reverse bias voltage		2	V	
5	Die binding temperature	-	350	C	(< 4 s) Note

Note: Recommended condition: 320 C max and 4 s max.



Optical and Electrical Characteristics

Since the HL1361CPxx is a chip form, the performance will depend on not only chip performance but also its assembling process. If the chip is assembled in a proper way, the performance described in Table 3 can be expected but these are not guaranteed values.

Table 3. Expected Optical and Electrical Characteristics (Tc= -5C to 95C, unless otherwise specified, Condition at CoC (Chip on testing carrier))

No	Optical and Electrical Characteristics	Min	Тур	Max	Units	Notes
1	Wavelength range	1265 - 1340		nm	at operating output power	
2	Side-mode suppression ratio (SMSR), operating condition	35		dB		
3	Threshold current @ 25C	-	8	15	mA	
4	Threshold current @ 95C	-	20	28	mA	
5	Slope efficiency @ 25C, I=Ith+5mA to I=Ith+50mA		0.3	-	W/A	
6	Slope efficiency @ 95C, I=Ith to I=70mA		-	-	W/A	
7	Mask Margin (IEEE 10.3Gb/s) I=Ith+25mA @25C	20	-	-	%	PRBS=2 ³¹ -1, 1k waveforms ER=4.5dB
8	Effective serial resistance I=50mA@ 95C	' -	7	' -	Ohms	
9	Laser forward voltage I=70mA@ 95C		1.5	2.0	V	
10	Kink deviation, Ith+5 to 100mA	-	1	20	%	See figure 5
11	Far field divergence angle, vertical, I=70mA@ 95C		35	45	degrees	
12	Far field divergence angle, horizontal, I=70mA@ 95C	-	32	40	degrees	

Note: Tc means sub-mount temperature when the chip mounted on Oclaro standard sub-mount soldered on a heat sink.

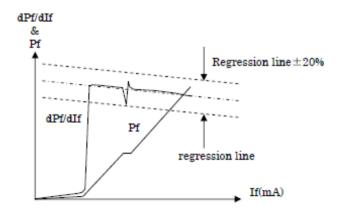


Fig 5 Kink definition



Chip Test Specification

Oclaro (supplier) will perform 100% probe testing on the chips described in Table 4 below. Only chips that pass the criteria in Table 4 will be shipped. The test will be done in bar or chip form using pulsed driving current.

Although chips pass the criteria described in Table 4, Oclaro assumes no responsibility for those performance, yield and reliability when they are assembled and/or tested in customer (buyer). Ts means stage temperature in pulse chip test.

Table 4 Chip test criteria

No.	Parameter	Symbol	Condition	Min	Max	Unit	Remark
1	Threshold current	I_{th}	$T_s=85^{\circ}C$	-	21.5	mA	Note1
2	Slope efficiency	Eta	T _s =85°C,	0.087	-	W/A	Note2
			$I_F=67.5\text{mA}$				
3	Peak wavelength	λ_{p}	$T_s=25$ °C	1288.8	1332.3	nm	
			$I_F=67.5mA$				
4	Side mode suppression ratio	SMSR	T _s =25°C I _F =67.5mA	35	-	dB	
			$T_s=85^{\circ}C$	35	-	dB	
			$I_F=67.5\text{mA}$				

Note1 21.5mA=28mA x A, A= Temperature correlated factor 0.782 Note2 0.087W/A=0.11W/A x B, B= Tester correlated factor 0.792



Wafer Verification Test

Oclaro will perform hard screening (Burn-In), DC measurement and AC measurement using chips mounted on Oclaro standard submount soldered on heat sink. Only the chips that passed the criteria described in this "Wafer Verification Test" section will be used. Only the chips from wafers meeting the minimum yield described in Table 5 will be shipped.

Table 5 Criteria in wafer verification test

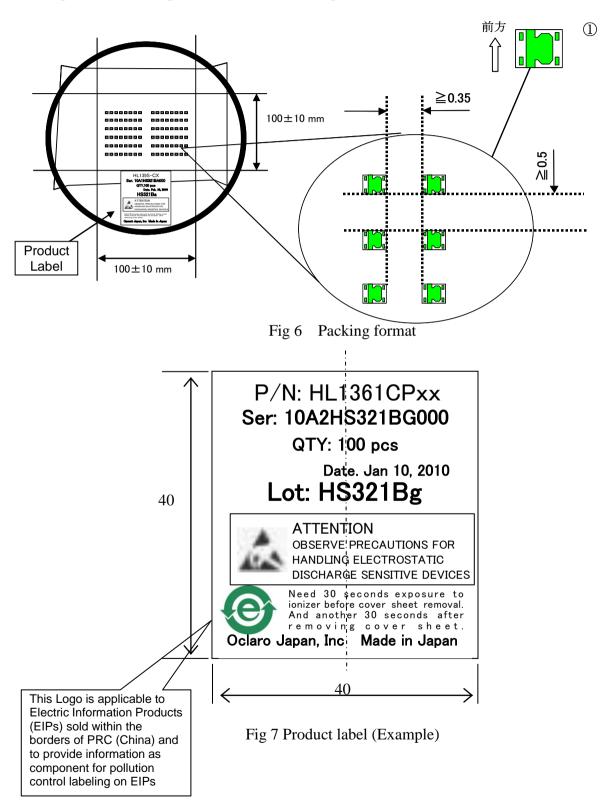
Parameter	Condition	Pass Criterion	Minimum Number or
			Yield
LD chip mount	-	-	20pcs
Start Burn-In test			
Optical Purge test	25°C, 120mA, ACC 3min.	$ \Delta I_{th} \le +5\%, \Delta Po $	
		$\leq +10\%$, $ \Delta Eta \leq +10\%$.	
Electrical Purge test	100°C, 150mA, ACC 20h	-	
APC Test	95°C, 70mA, APC 100h,	$-2\% \le \Delta I_{op} \le +0.5\%$	
	$(I_{op}@100h-I_{op}@0h/I_{op}@0h$		
Pass Burn-In test			
Start DC test			
Threshold current	T _c =95°C	I _{th} ≤28mA	
Slope efficiency	T _c =95°C,	Eta≥0.11W/A	1
,	Eta=Po(70mA)/(70mA- I_{th})		
Forward voltage	$T_c=1$ °C, $I_o=33$ mA	V _{op} ≤1.8V	
	$T_c=95$ °C, $I_o=70$ mA	op 	
Kink deviation,	$T_c=1$ °C and 95°C, Ith+5 to	kink free	
	100mA		
Peak wavelength	$T_c=1$ °C, $I_o=33$ mA	1285.2 nm≤λp≤1337.5nm	
C	T _c =95°C, I _o =70mA	1285.2 nm≤λp≤1337.5 nm	
Side mode	$T_c=1^{\circ}C$, $Io=33mA$	SMSR≥35dB	
suppression ratio	$T_c=95$ °C, $I_o=70$ mA		
Beam divergence	T _c =95°C, I _o =70mA	FWHM_H≤36deg	
angle (Horizontal)			
Beam divergence	T _c =95°C, I _o =70mA	FWHM_V≤40deg	
angle (Vertical)			
Pass DC test			10 of 20pcs
			(50%)



OTHER SPECIFICATIONS

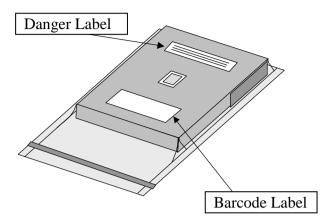
Packing and label

The products will be packed as described in Fig. 6 below.



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The plastic bag is vacuum-packed.

Fig 8 Packing bag (Example)

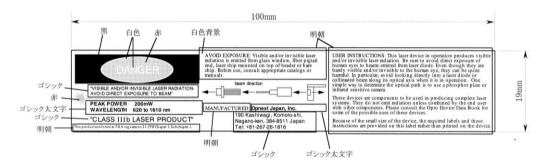


Fig 9 Danger Label (Example)

Bar code label is on plastic bag for each shipment form. Supplier Product Name, Supplier lot number, the Quantity and Customer Part Number are on it. Please see Fig. 8. 40x 80 mm

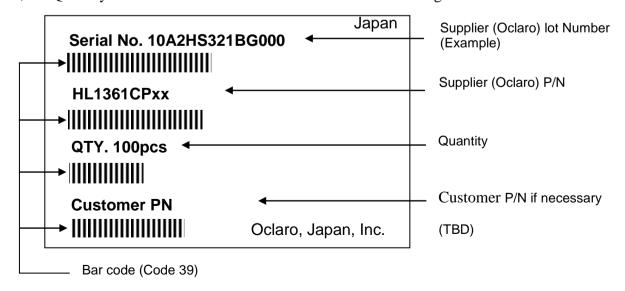


Fig. 8 Bar code label on outer plastic bag (Example of HL1361CPxx)



Revision History

Rev	Date	Page/Line/Fig/Table	Modification	Note
•				
0.0	Jul, 30, 2014			